

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74ACT273P, TC74ACT273F, TC74ACT273FW

OCTAL D-TYPE FLIP FLOP WITH CLEAR

(Note) The JEDEC SOP (FW) is not available in Japan.

The TC74ACT273 is an advanced high speed CMOS OCTAL D-TYPE FLIP FLOP fabricated with silicon gate and double-layer metal wiring C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

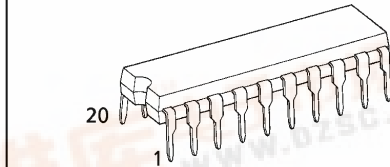
Information signals applied to D inputs are transferred to the Q outputs on the positive going edge of the clock pulse.

When the $\overline{\text{CLR}}$ input is held "L", the Q outputs are at a low logic level independent of the other inputs.

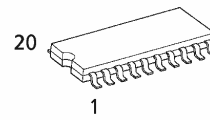
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

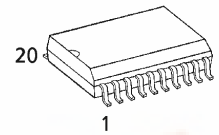
- High Speed..... $f_{\text{MAX}} = 170\text{MHz}(\text{typ.})$
at $V_{\text{CC}} = 5\text{V}$
- Low Power Dissipation..... $I_{\text{CC}} = 8\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs.... $V_{\text{IL}} = 0.8\text{V}(\text{Max.})$
 $V_{\text{IH}} = 2.0\text{V}(\text{Min.})$
- Symmetrical Output Impedance... $|I_{\text{OH}}| = I_{\text{OL}} = 24\text{mA}(\text{Min.})$
Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays.... $t_{\text{pLH}} \approx t_{\text{pHL}}$
- Pin and Function Compatible with 74F273



P (DIP20-P-300-2.54A)
Weight : 1.30g (Typ.)

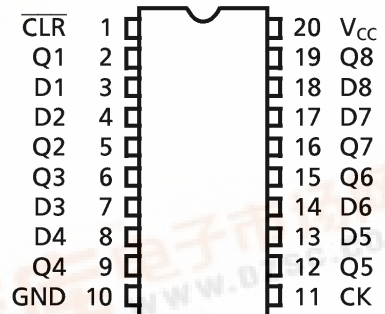


F (SOP20-P-300-1.27)
Weight : 0.22g (Typ.)



FW (SOL20-P-300-1.27)
Weight : 0.46g (Typ.)

PIN ASSIGNMENT



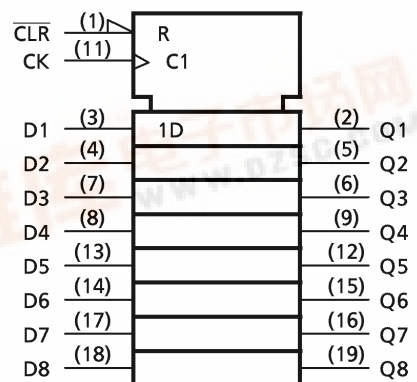
(TOP VIEW)

TRUTH TABLE

INPUTS			OUTPUTS	FUNCTION
$\overline{\text{CLR}}$	D	CK	Q	
L	X	X	L	CLEAR
H	L		L	—
H	H		H	—
H	X		Q _n	NO CHANGE

X : Don't care

IEC LOGIC SYMBOL

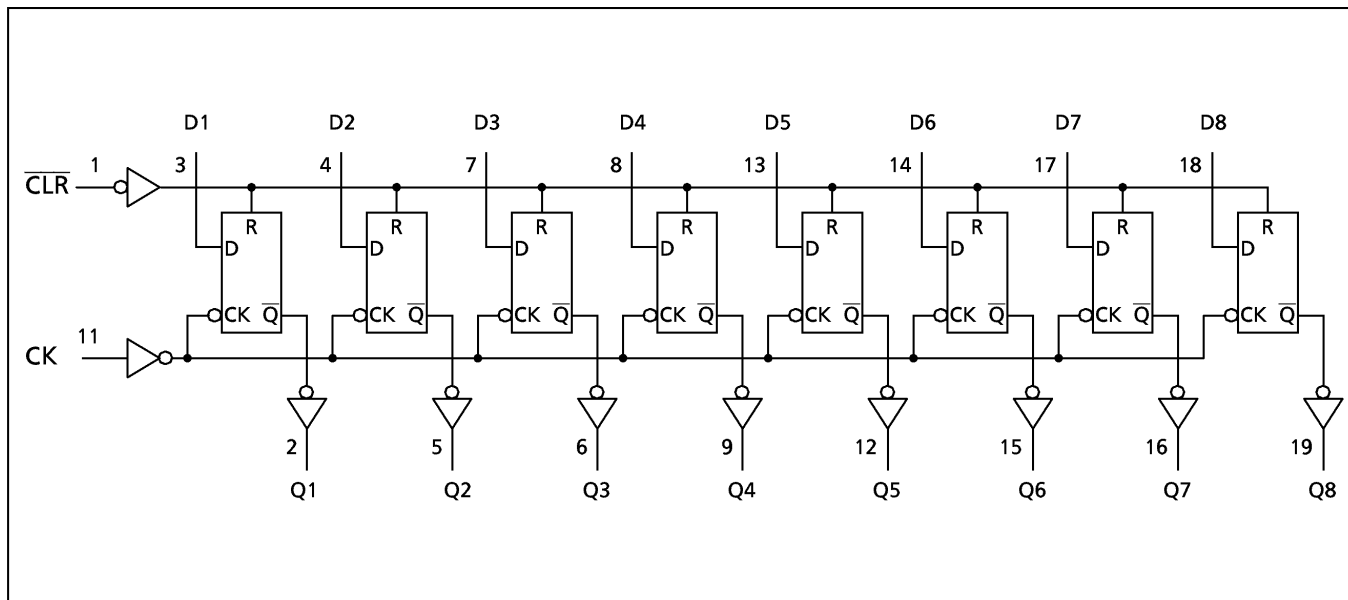


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SYSTEM DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 200	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}C \sim 65^{\circ}C$. From $T_a = 65^{\circ}C$ to $85^{\circ}C$ a derating factor of $-10mW/^{\circ}C$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	4.5~5.5	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	dt / dV	0~10	ns / V

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V _{IH}			4.5 5	2.0	—	—	2.0	—	V
Low - Level Input Voltage	V _{IL}			4.5 5.5	—	—	0.8	—	0.8	V
High - Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA I _{OH} = -24mA I _{OH} = -75mA*	4.5 4.5 5.5	4.4 3.94 —	4.5 — —	— — —	4.4 3.80 3.85	— — —	V
Low - Level Output Voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA I _{OL} = 24mA I _{OL} = 75mA*	4.5 4.5 5.5	— — —	0.0 — —	0.1 0.36 —	— — —	0.1 0.44 1.65	V
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND		5.5	—	—	±0.1	—	±1.0	μA
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	8.0	—	80.0	
	I _C	PER INPUT : V _{IN} = 3.4V OTHER INPUT : V _{CC} or GND		5.5	—	—	1.35	—	1.5	mA

* : This spec indicates the capability of driving 50Ω transmission lines.

One output should be tested at a time for a 10ms maximum duration.

TIMING REQUIREMENTS (Input t_r = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C		Ta = -40~85°C		UNIT
			V _{CC} (V)	LIMIT	LIMIT	LIMIT	
Minimum Pulse Width (CK)	t _{W(L)} t _{W(H)}		5.0 ± 0.5	5.0	5.0	ns	
Minimum Pulse Width (CLR)	t _{W(L)}		5.0 ± 0.5	5.0	5.0		
Minimum Set - up Time	t _s		5.0 ± 0.5	3.5	3.5		
Minimum Hold Time	t _h		5.0 ± 0.5	1.5	1.5		
Minimum Removal Time (CLR)	t _{rem}		5.0 ± 0.5	3.0	3.0		

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, $R_L = 500\ \Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time (CK-Q)	t _{pLH} t _{pHL}		5.0 ± 0.5	—	6.6	10.5	1.0	12.0	ns
Propagation Delay Time ($\overline{\text{CLR}}$ -Q)	t _{pHL}		5.0 ± 0.5	—	7.4	10.8	1.0	12.3	
Maximum Clock Frequency	f _{MAX}		5.0 ± 0.5	80	150	—	80	—	MHz
Input Capacitance	C _{IN}			—	5	10	—	10	pF
Power Dissipation Capacitance	C _{PD} (1)			—	34	—	—	—	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

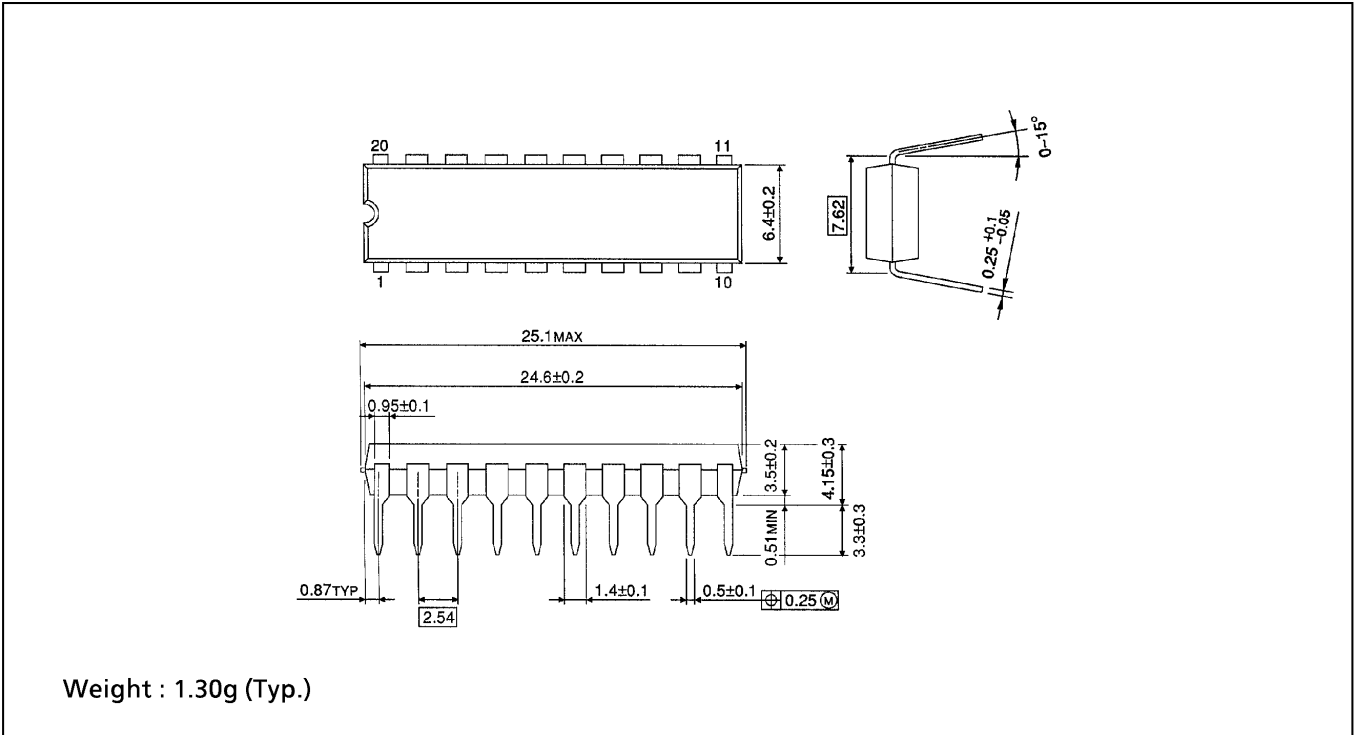
$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8 \text{ (per F/F)}$$

And the total C_{PD} when n pcs. of Flip Flop operate can be gained by the following equation :

$$C_{PD}(\text{total}) = 23 + 11 \cdot n$$

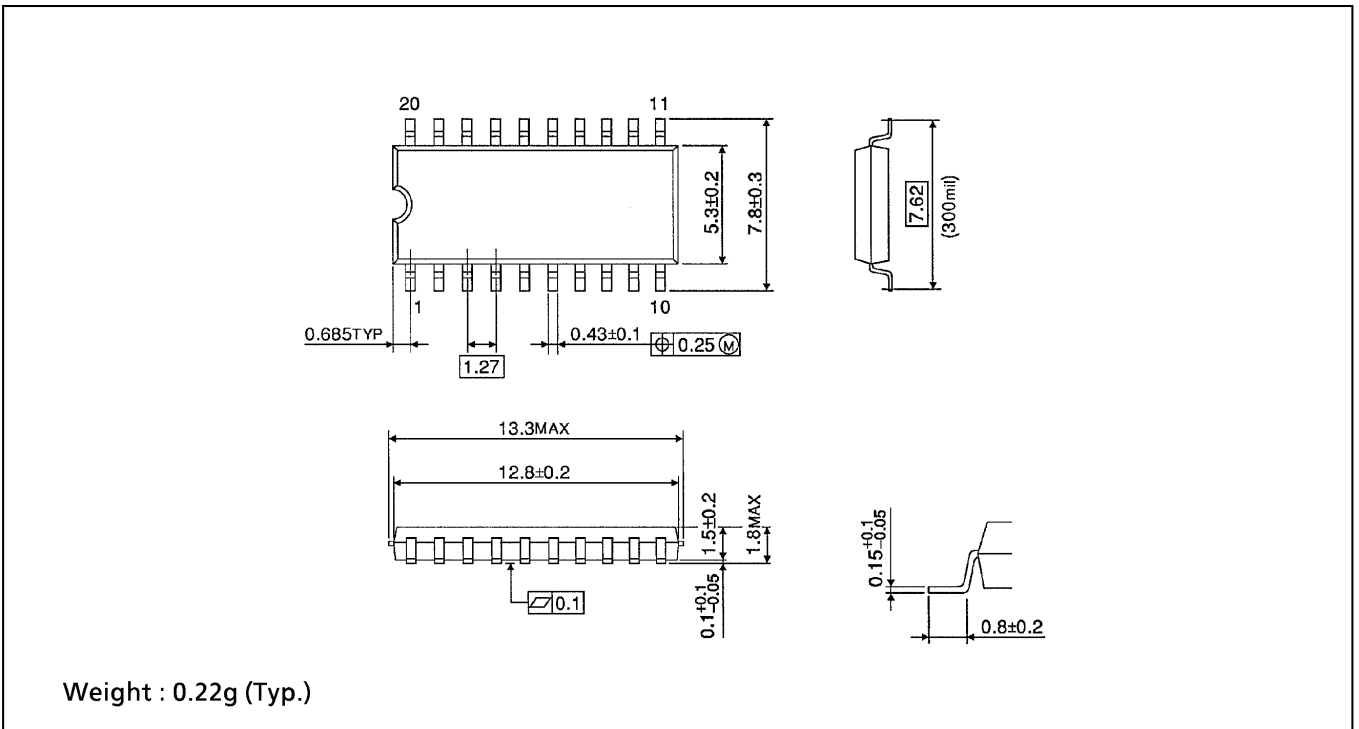
DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

Unit in mm



SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

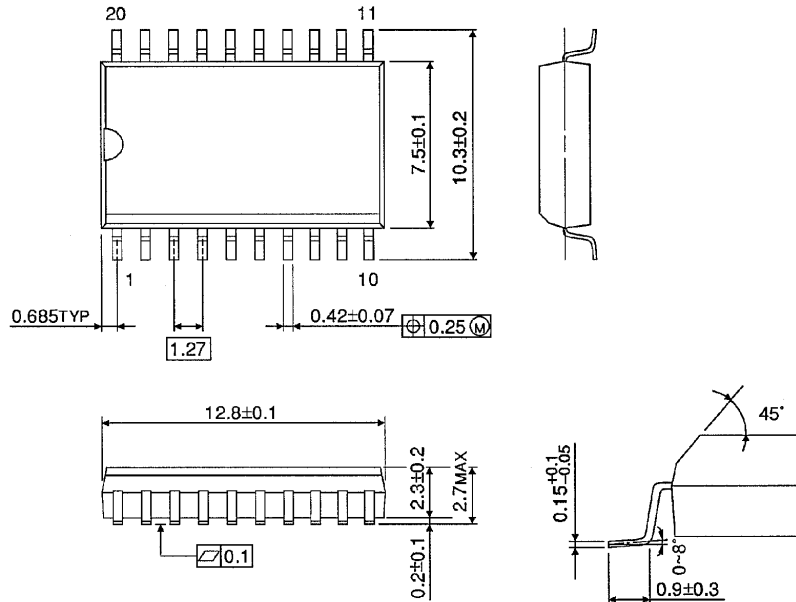
Unit in mm



SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)